QUAD 2-INPUT NAND GATE

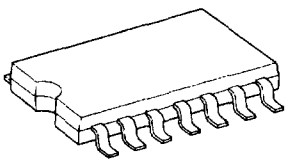
The TC74LVQ00 is a high speed CMOS 2-INPUT NAND GATE fabricated with silicon gate and double-layer metal wiring C^2MOS technology.

Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.

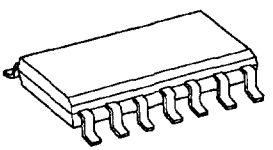
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

TC74LVQ00F



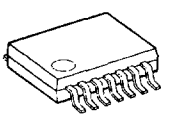
SOP14-P-300

TC74LVQ00FN



SOL14-P-150

TC74LVQ00FS



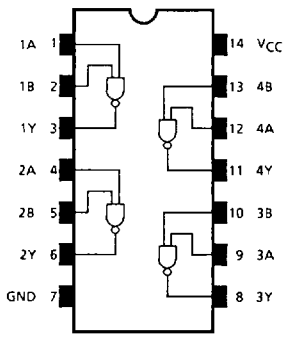
SSOP14-P-225

Weight SOP14-P-300 : 0.18g (Typ.)
SOL14-P-150 : 0.12g (Typ.)
SSOP14-P-225 : 0.07g (Typ.)

FEATURES

- High speed : $t_{pd} = 4.9ns$ (Typ.) ($V_{CC} = 3.3V$)
- Low power dissipation : $I_{CC} = 2.5\mu A$ (Max.) ($Ta = 25°C$)
- Input voltage level : $V_{IL} = 0.8V$ (Max.) ($V_{CC} = 3V$)
  $V_{IH} = 2.0V$ (Min.) ($V_{CC} = 3V$)
- Symmetrical output impedance
  : $|I_{OH}| = I_{OL} = 12mA$ (Min.)
- Balanced propagation delays
  : $t_{pLH} \simeq t_{pHL}$
- Pin and function compatible with 74HC00

PIN ASSIGNMENT

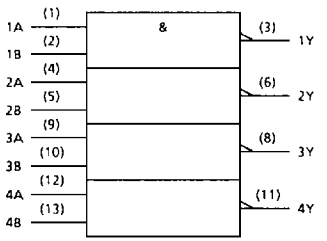


(TOP VIEW)

TRUTH TABLE

INPUTS		OUTPUTS
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L

IEC LOGIC SYMBOL



MAXIMUM RATINGS

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage Range	V_{CC}	−0.5~7.0	V
DC Input Voltage	V_{IN}	−0.5~V_{CC}+0.5	V
DC Output Voltage	V_{OUT}	−0.5~V_{CC}+0.5	V
Input Diode Current	I_{IK}	±20	mA
Output Diode Current	I_{OK}	±50	mA
DC Output Current	I_{OUT}	±50	mA
DC V_{CC}/Ground Current	I_{CC}	±100	mA
Power Dissipation	P_D	180	mW
Storage Temperature	T_{stg}	−65~150	°C
Lead Temperature 10s	T_L	300	°C

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V_{CC}	2.0~3.6	V
Input Voltage	V_{IN}	0~V_{CC}	V
Output Voltage	V_{OUT}	0~V_{CC}	V
Operating Temperature	T_{opr}	−40~85	°C
Input Rise And Fall Time	dt/dv	0~100	ns/v

ELECTRICAL CHARACTERISTICS

DC characteristics

PARAMETER		SYMBOL	TEST CONDITION		V_{CC} (V)	Ta = 25°C			Ta = −40~85°C		UNIT
						MIN.	TYP.	MAX.	MIN.	MAX.	
Input Voltage	"H" Level	V_{IH}			3.0	2.0	—	—	2.0	—	V
	"L" Level	V_{IL}			3.0	—	—	0.8	—	0.8	
Output Voltage	"H" Level	V_{OH}	V_{IN} = V_{IH} or V_{IL}	I_{OH} = −50μA	3.0	2.9	3.0	—	2.9	—	V
				I_{OH} = −12mA	3.0	2.58	—	—	2.48	—	
	"L" Level	V_{OL}	V_{IN} = V_{IH}	I_{OL} = 50μA	3.0	—	0.0	0.1	—	0.1	
				I_{OL} = 12mA	3.0	—	—	0.36	—	0.44	
Input Leakage Current		I_{IN}	V_{IN} = V_{CC} or GND		3.6	—	—	±0.1	—	±1.0	μA
Quiescent Supply Current		I_{CC}	V_{IN} = V_{CC} or GND		3.6	—	—	2.5	—	25.0	μA

AC characteristics (Input $t_r = t_f$ = 3ns, C_L = 50pF, R_L = 500Ω)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	Ta = 25°C			Ta = −40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time	t_{pLH}		2.7	—	7.0	13.4	1.0	16.0	ns
	t_{pHL}		3.3±0.3	—	5.8	9.5	1.0	11.0	
Output To Output Skew	t_{osLH}	(Note 1)	2.7	—	—	1.5	—	1.5	ns
	t_{osHL}		3.3±0.3	—	—	1.5	—	1.5	
Input Capacitance	C_{IN}	(Note 2)		—	5	10	—	10	pF
Power Dissipation Capacitance	C_{PD}	(Note 3)		—	30	—	—	—	pF

(Note 1) Parameter guaranteed by design.
($t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLm} - t_{pHLn}|$)

(Note 2) Parameter guaranteed by design.

(Note 3) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption.
Average operating current can be obtained by the equation :
$I_{CC}(opr.) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4$ (per Gate)

Noise characteristics (Ta = 25°C, Input $t_r = t_f$ = 3ns, C_L = 50pF, R_L = 500Ω)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	TYP.	LIMIT	UNIT
Quiet Output Maximum Dynamic V_{OL}	V_{OLP}		3.3	0.3	0.8	V
Quiet Output Minimum Dynamic V_{OL}	V_{OLV}		3.3	−0.3	−0.8	V
Minimum High Level Dynamic Input Voltage	V_{IHD}		3.3	—	2.0	V
Maximum Low Level Dynamic Input Voltage	V_{ILD}		3.3	—	0.8	V